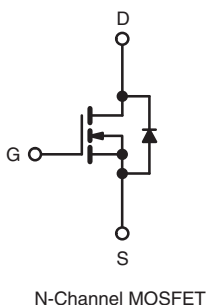
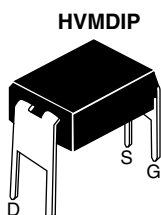


Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	60	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.8
Q_g (Max.) (nC)	7	
Q_{gs} (nC)	2	
Q_{gd} (nC)	7	
Configuration	Single	



FEATURES

- For Automatic Insertion
- Compact Plastic Package
- End Stackable
- Fast Switching
- Low Drive Current
- Easily Paralleled
- Excellent Temperature Stability
- Compliant to RoHS Directive 2002/95/EC

Note

* Pb containing terminations are not RoHS compliant, exemptions may apply



RoHS*
COMPLIANT

DESCRIPTION

The HVMDIP technology is the key to Vishay's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HVMDIP design achieves very low on-state resistance combined with high transconductance and extreme device ruggedness. HVMDIPs feature all of the established advantages of MOSFETs such as voltage control, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

The HVMDIP 4 pin, dual-in-line package brings the advantages of HVMDIPs to high volume applications where automatic PC board insertion is desirable, such as circuit boards for computers, printers, telecommunications equipment, and consumer products. Their compatibility with automatic insertion equipment, low-profile and end stackable features represent the state-of-the-art in power device packaging.

ORDERING INFORMATION

Package	HVMDIP
Lead (Pb)-free	IRFD113PbF
	SiHFD113-E3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage ^a	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	0.8	A
Pulsed Drain Current ^b	I_{DM}	6.4	
Linear Derating Factor		0.008	W/ $^{\circ}\text{C}$
Inductive Current, Clamped	I_{LM}	6.4	A
Maximum Power Dissipation	P_D	1.0	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^{\circ}\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s	300 $^{\circ}\text{C}$	

Notes

- $T_J = 25\text{ }^{\circ}\text{C}$ to $150\text{ }^{\circ}\text{C}$
- Repetitive rating; pulse width limited by maximum junction temperature.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	120	°C/W

SPECIFICATIONS ($T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 500	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = max. rating, V _{GS} = 0 V		-	-	250	μA
		V _{DS} = max. rating x 0.8, V _{GS} = 0 V, T _C = 125 °C		-	-	1000	
On-State Drain Current ^b	I _{D(on)}	V _{GS} = 10 V	V _{DS} > I _{D(on)} x R _{DS(on)} max.	0.8	-	-	A
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V	I _D = 0.8 A	-	0.6	0.8	Ω
Forward Transconductance ^b	g _{fs}	V _{DS} > I _{D(on)} x R _{DS(on)} max., I _D = 0.8 A		0.8	1.2	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz		-	135	200	pF
Output Capacitance	C _{oss}			-	80	100	
Reverse Transfer Capacitance	C _{rss}			-	20	25	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 4 A, V _{DS} = 0.8 max. rating	-	5	7	nC
Gate-Source Charge	Q _{gs}			-	2	-	
Gate-Drain Charge	Q _{gd}			-	7	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 0.5 V _{DS} , I _D = 0.8 A, R _g = 50 Ω		-	10	20	ns
Rise Time	t _r			-	15	25	
Turn-Off Delay Time	t _{d(off)}			-	15	25	
Fall Time	t _f			-	10	20	
Internal Drain Inductance	L _D	Between lead, 2 mm (0.08") from package and center of die contact		-	4.0	-	nH
Internal Source Inductance	L _S			-	6.0	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	0.8	A
Pulsed Diode Forward Current	I _{SM}			-	-	6.4	
Body Diode Voltage ^a	V _{SD}	T _A = 25 °C, I _S = 0.8 A, V _{GS} = 0 V		-	-	2	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 150 °C, I _F = 1.0 A, dI/dt = 100 A/μs		-	100	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	0.2	-	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

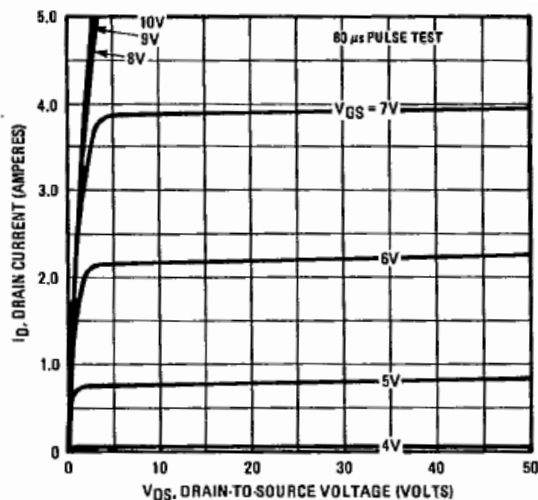
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


Fig. 1 - Typical Output Characteristics

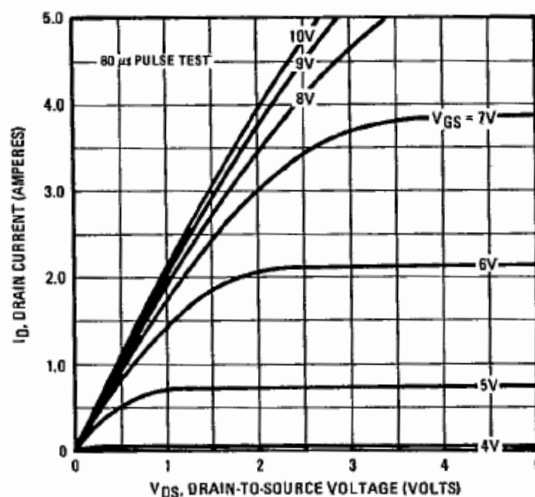


Fig. 3 - Typical Saturation Characteristics

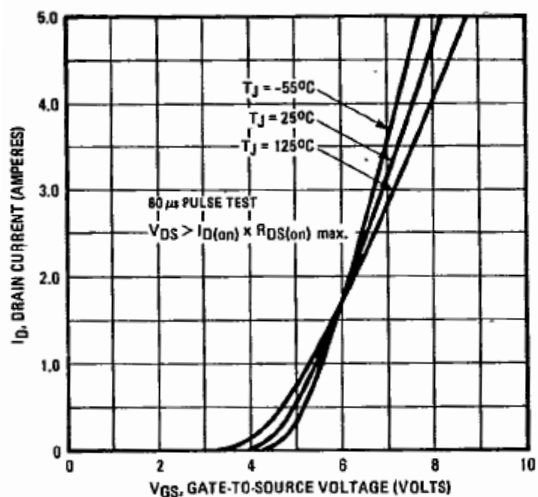


Fig. 2 - Typical Transfer Characteristics

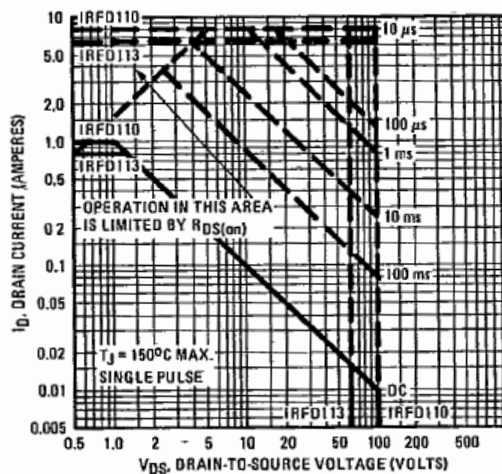


Fig. 4 - Maximum Safe Operating Area

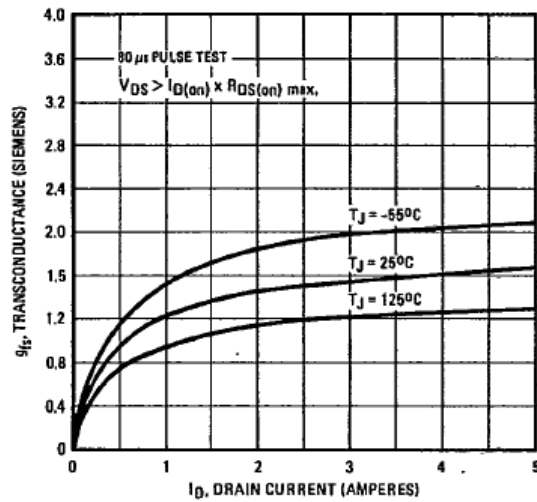


Fig. 5 - Typical Transconductance vs. Drain Current

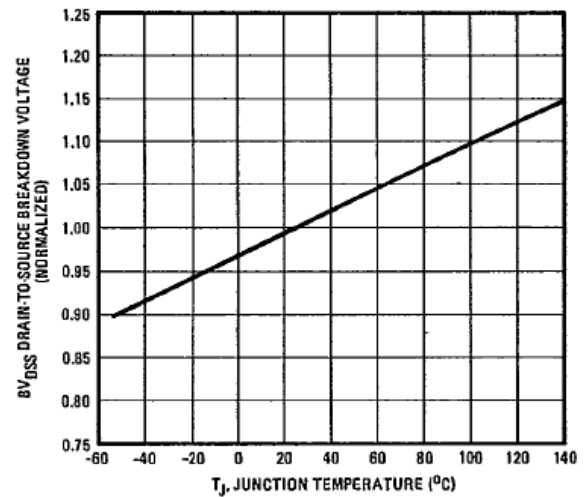


Fig. 7 - Breakdown Voltage vs. Temperature

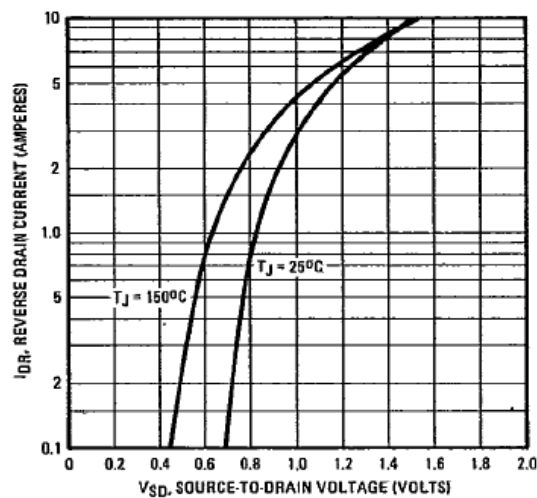


Fig. 6 - Typical Source-Drain Diode Forward Voltage

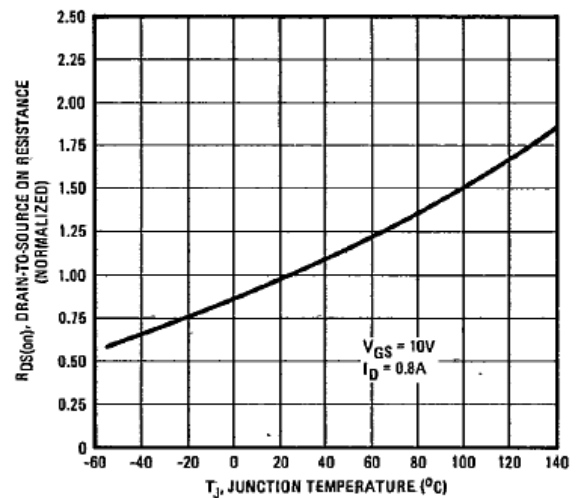


Fig. 8 - Normalized On-Resistance vs. Temperature

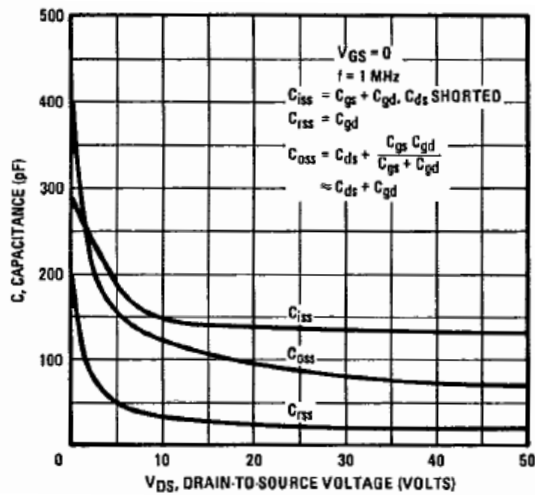


Fig. 9 - Typical Capacitance vs. Drain-to-Source Voltage

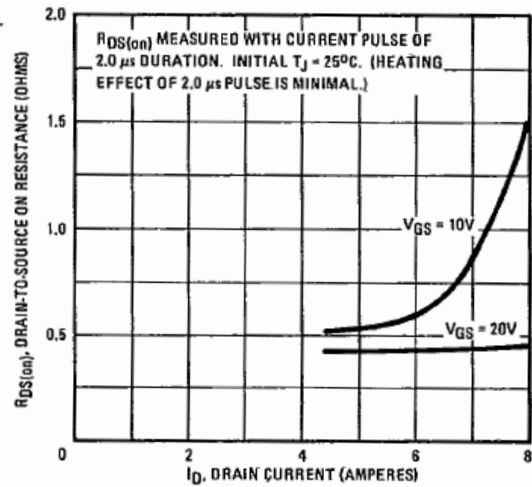


Fig. 11 - Typical On-Resistance vs. Drain Current

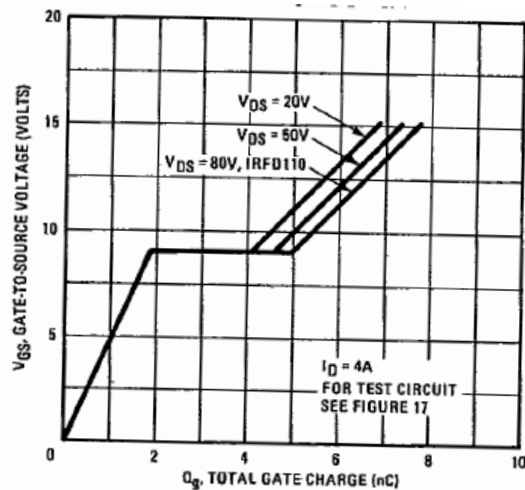


Fig. 10 - Typical Gate Charge vs. Gate-to-Source Voltage

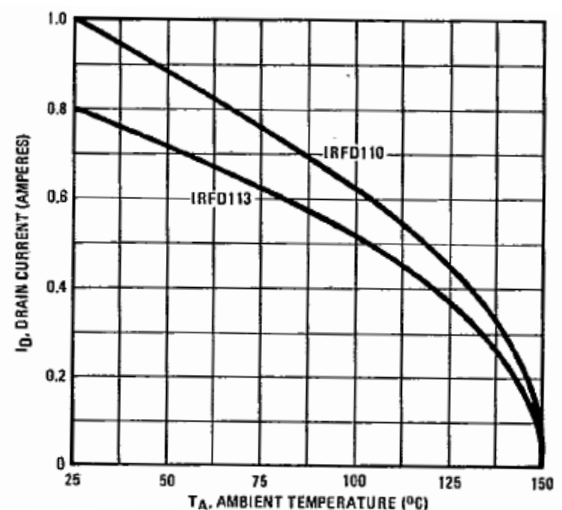
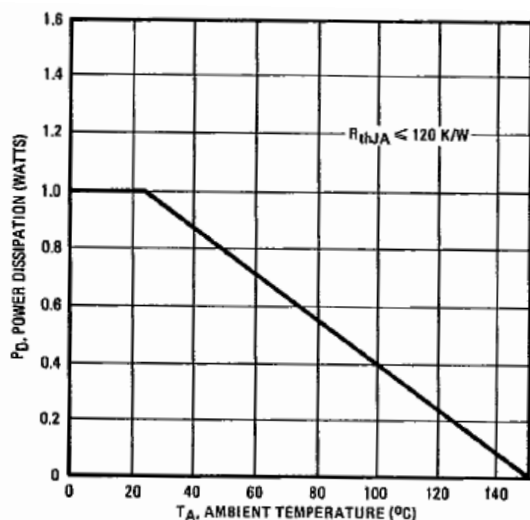
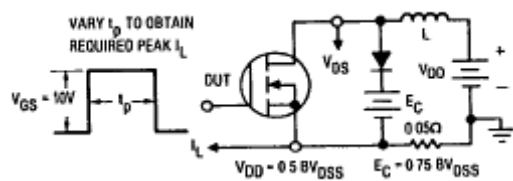
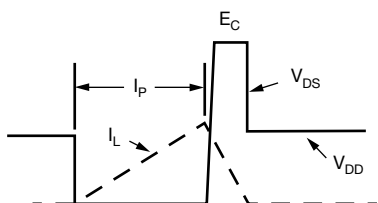
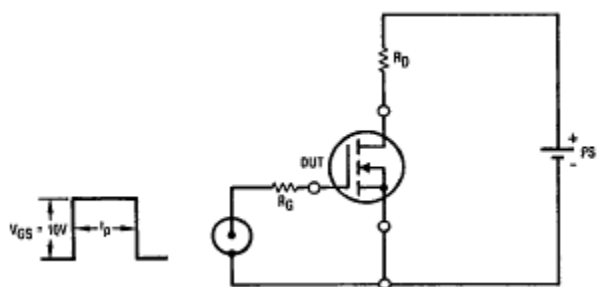
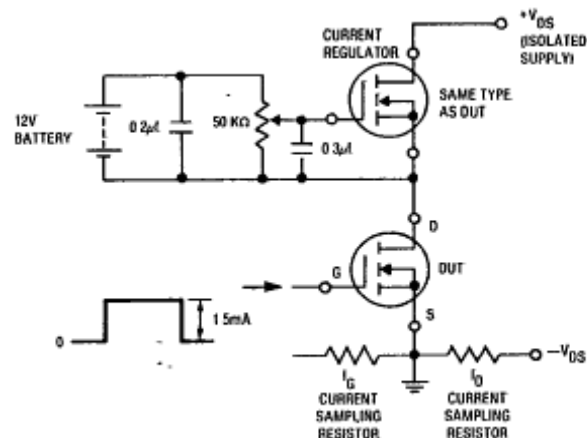
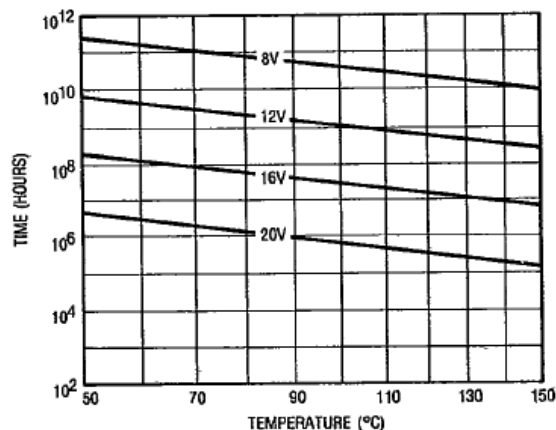
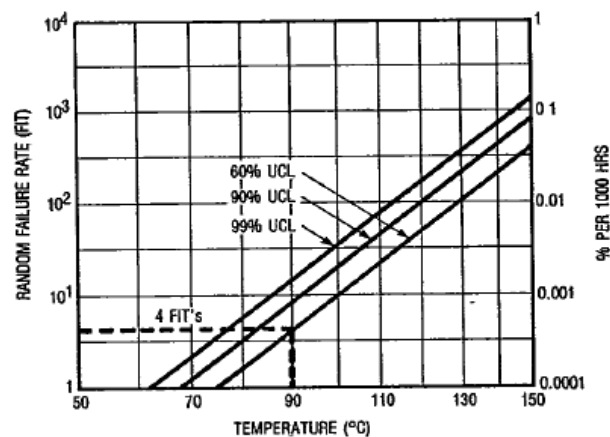
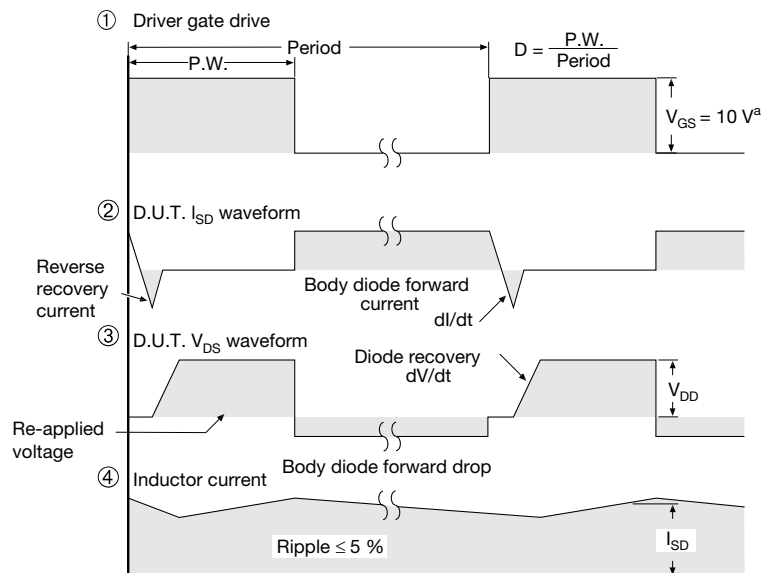
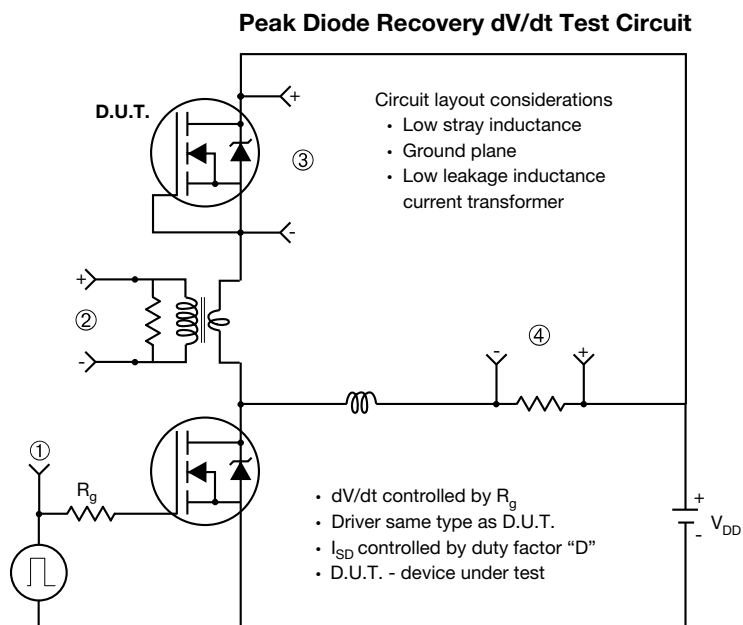


Fig. 12 - Maximum Drain Current vs. Case Temperature


Fig. 13 - Power vs. Temperature Derating

Fig. 14 - Clamped Inductive Test Circuit

Fig. 15 - Clamped Inductive Waveforms

Fig. 16 - Switching Time Test Circuit

Fig. 17 - Gate Charge Test Circuit

Fig. 18 - Typical Time to Accumulated 1 % Gate Failure

Fig. 19 - Typical High Temperature Reverse Bias (HTRB) Failure Rate



Note

a. $V_{GS} = 5 \text{ V}$ for logic level devices

Fig. 20 - For N-Channel

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